PRODUCT NAME : 2N5306 NPN Darlington Transistor (Pack of 5)

PRICE : Rs 20.00
SKU : RM2079

DESCRIPTION

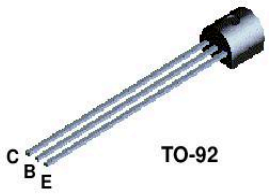
Features

- Collector-Emitter Volt (Vceo): 25V
- Collector-Base Volt (Vcbo): 25V
- Collector Current (Ic): 1.2A
- hfe: 7,000-70,000 @ 2mA
- Power Dissipation (Ptot): 625mW
- Type: PNP

FAIRCHILD SEMICONDUCTOR™

Discrete POWER & Signal Technologies

2N5306



NPN Darlington Transistor

This device is designed for applications requiring extremely high current gain at currents to 1.0 A. Sourced from Process 05. See MPSA14 for characteristics.

Absolute Maximum Ratings*

TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V_{CEO}	Collector-Emitter Voltage	25	V
V_{CBO}	Collector-Base Voltage	25	V
V_{EBO}	Emitter-Base Voltage	12	V
I_C	Collector Current - Continuous	1.2	A
T_J, T_{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:
1) These ratings are based on a maximum junction temperature of 150 degrees C.
2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics

TA = 25°C unless otherwise noted

Symbol	Characteristic	Max	Units
		2N5306	
P_D	Total Device Dissipation Derate above 25°C	625 5.0	mW mW/°C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	83.3	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	200	°C/W